

Silicon Epitaxial Base Mesa Transistor

T-33-21
T-33-11

**2SA1060 (PNP)
2SC2484 (NPN)**

TOP-3 Package (See Page 36 For Dimensions)

2SA1060 (PNP)

Absolute Maximum Ratings (Ta=25°C)

Item	Symbol	Rating	Unit
Collector-Base Voltage	-Vcbo	80	V
Collector-Emitter Voltage	-Vceo	80	V
Emitter-Base Voltage	-Veb0	5	V
Collector Current	-Ic	5	A
Peak Collector Current	-Icm	8	A
Collector Power Dissipation	Pc*	60	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~+150	°C

*Tc=25°C

High Power Audio Frequency Amplifier
Complementary Pair with 2SC2484

Feature

• High collector power dissipation: 60W(Tc=25°C)

**hFE Classification

hFE	100~200	60~120	40~80
Class	P	Q	R

Electrical Characteristics (Ta=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector Cutoff Current	-Icbo	-Vcb=80V, Ie=0			50	μA
Emitter Cutoff Current	-Iebo	-Veb=3V, Ic=0			50	μA
DC Current Gain	hFE1	-Vce=5V, -Ic=0.02A	20			
	hFE2**	-Vce=5V, -Ic=1.0A	40		220	V
	hFE3	-Vce=5V, -Ic=3A	20			
Base Emitter Voltage	-Vbe	-Vce=5V, -Ic=3A			1.8	V
Collector-Emitter Saturation Voltage	-Vce(sat)	-Ic=3A, -Ib=0.3			2.0	V
Gain Bandwidth Product	ft	-Vce=5V, -Ic=0.5A		20		MHz

2SC2484 (NPN)

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Electrical Characteristics (Ta=25°C)

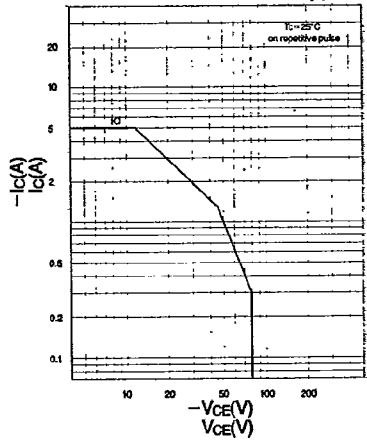
Item	Symbol	Condition	min.	typ.	max.	Unit
Collector Cutoff Current	Icbo	Vcb=80V, Ie=0			50	μA
Emitter Cutoff Current	Iebo	Veb=3V, Ic=0			50	μA
DC Current Gain	hFE1	Vce=5V, Ic=0.02A	20			
	hFE2**	Vce=5V, Ic=1.0A	40		220	V
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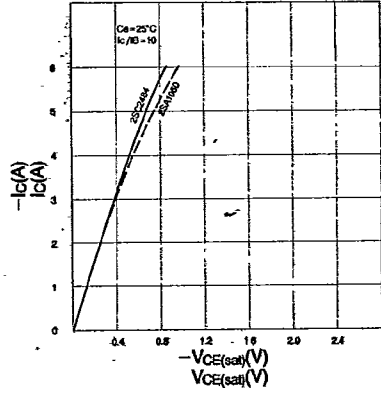
**2SA1060 (PNP)
2SC2484 (NPN)**

Typical Characteristics

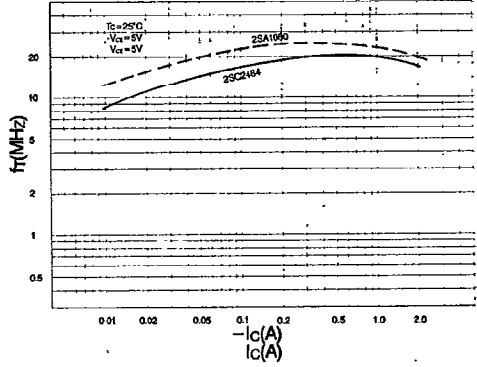
Area of Safe Operation (ASO) (Tc=25°C)



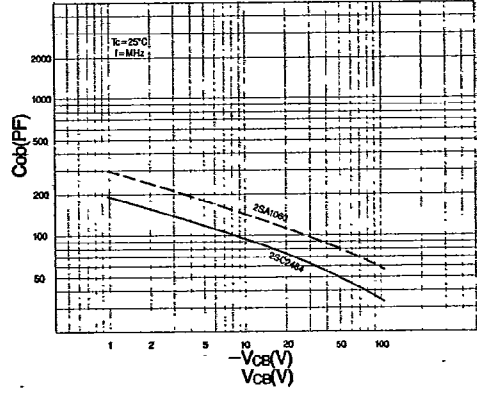
Vce(sat) vs. Ic characteristics



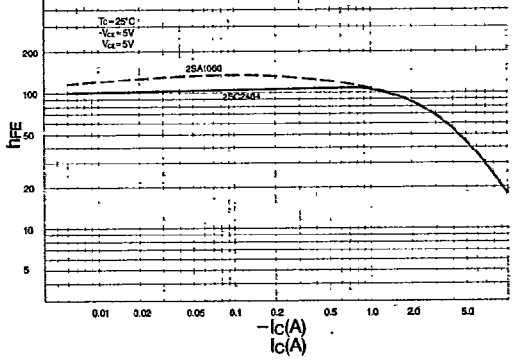
fT vs. Ic characteristics



Cob vs. Vce characteristics



hFE vs Ic characteristics



VBE vs. Ic characteristics

